

MOSFETs Silicon N-Channel MOS (π-MOSVIII)

TK5A90E

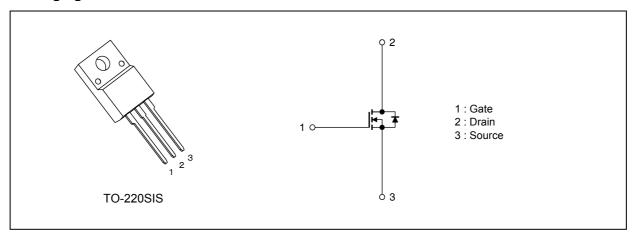
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance : $R_{DS(ON)} = 2.5 \Omega$ (typ.)
- (2) Low leakage current : $I_{DSS} = 10 \mu A \text{ (max)} \text{ (V}_{DS} = 720 \text{ V)}$
- (3) Enhancement mode : V_{th} = 2.5 to 4.0 V (V_{DS} = 10 V, I_{D} = 0.45 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	900	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	4.5	Α
Drain current (pulsed)	(Note 1)	I _{DP}	13.5	
Power dissipation ((T _c = 25 °C)	P_{D}	40	V
Single-pulse avalanche energy	(Note 2)	E _{AS}	202	mJ
Avalanche current		I _{AR}	4.5	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	4.5	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	13.5	
Channel temperature		T _{ch}	150	℃
Storage temperature		T _{stg}	-55 to 150	
Isolation voltage (RMS)	(t = 1.0 s)	V _{ISO(RMS)}	2000	V
Mounting torque		TOR	0.6	N·m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	3.125	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	62.5	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 18.3 mH, R_{G} = 25 Ω , I_{AR} = 4.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 720 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	900	_	_	V
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 0.45 mA	2.5	_	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 2.3 A	_	2.5	3.1	Ω

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V,	_	950	_	pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	_	8	_	
Output capacitance	C _{oss}		_	75	_	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	4.0	_	Ω
Switching time (rise time)	t _r	See Fig.6.2.1	_	25	_	ns
Switching time (turn-on time)	t _{on}		_	55	_	
Switching time (fall time)	t _f		_	15	_	
Switching time (turn-off time)	t _{off}		_	80	_	
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 4.5 A	15			V/ns

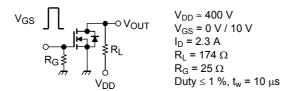


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	9	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V},$	_	20	_	nC
Gate-source charge 1	Q _{gs1}	I _D = 4.5 A	_	7	_	
Gate-drain charge	Q_{gd}		_	10	_	

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I _{DR} = 4.5 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time		$I_{DR} = 4.5 \text{ A}, V_{GS} = 0 \text{ V},$		1000	_	ns
Reverse recovery charge	Q _{rr}	-dl _{DR} /dt = 100 A/μs		6.5	_	μС
Peak reverse recovery current	Irr		_	18		Α



7. Marking (Note)

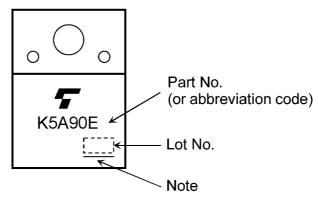


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

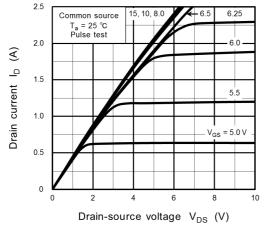
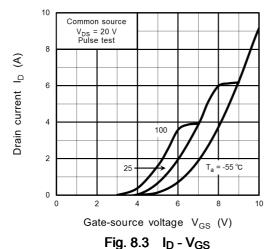


Fig. 8.1 I_D - V_{DS}



I_D = 10 iii. Pulse test Drain-source voltage V_{DSS} 980 920 860 800 L -100

1100

1040

 \leq

Common source $V_{GS} = 0 \text{ V}$ $I_D = 10 \text{ mA}$

Ambient temperature T_a (°C) Fig. 8.5 V_{DSS} - T_a

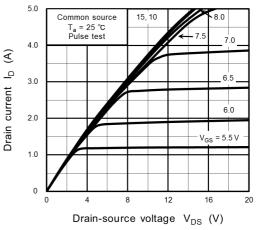
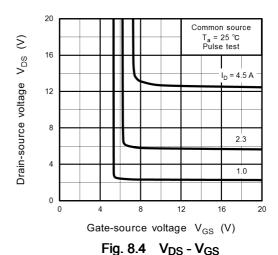


Fig. 8.2 I_D - V_{DS}



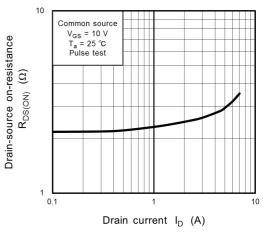
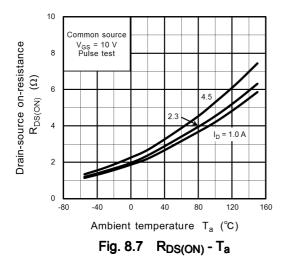


Fig. 8.6 R_{DS(ON)} - I_D



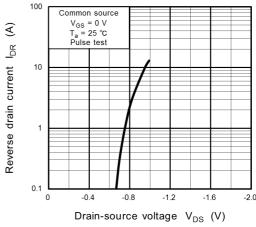
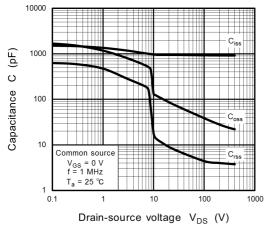


Fig. 8.8 I_{DR} - V_{DS}



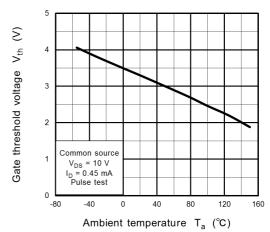
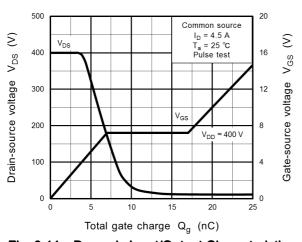


Fig. 8.9 C - V_{DS}

Fig. 8.10 V_{th} - T_a



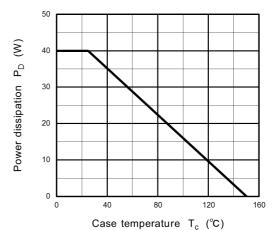


Fig. 8.11 Dynamic Input/Output Characteristics

Fig. 8.12 P_D - T_c (Guaranteed Maximum)

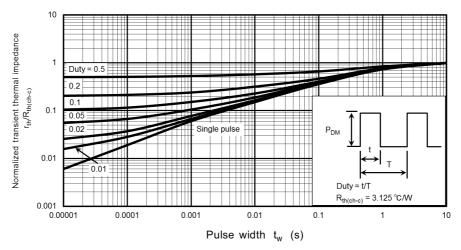


Fig. 8.13 $r_{th}/R_{th(ch-c)} - t_w$ (Guaranteed Maximum)

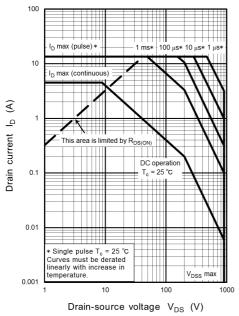


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

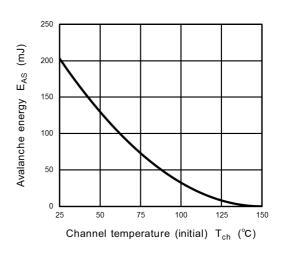


Fig. 8.15 E_{AS} - T_{ch} (Guaranteed Maximum)

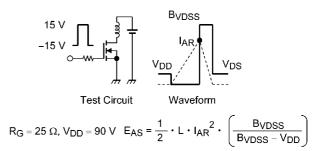


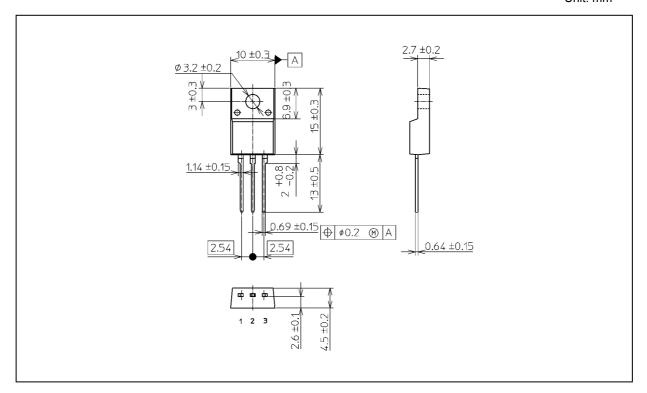
Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.7 g (typ.)

Pa	ckage Name(s)
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	



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